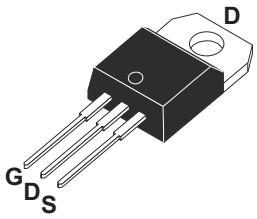
N-Channel Power MOSFET
(4A, 800Volts)

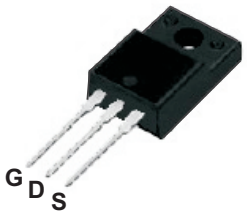
DESCRIPTION

The Nell **4N80** is a three-terminal silicon device with current conduction capability of 4A, fast switching speed, low on-state resistance, breakdown voltage rating of 800V ,and max. threshold voltage of 5 volts.

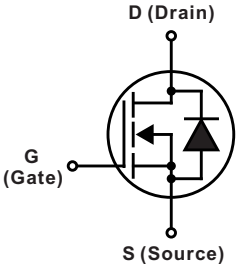
They are designed for use in applications. such as switched mode power supplies, DC to DC converters, **PWM** motor controls, bridge circuits, and general purpose switching applications .



TO-220AB
(4N80A)



TO-220F
(4N80AF)



FEATURES

- $R_{DS(ON)}$ = 3.6Ω @ V_{GS} = 10V
- Ultra low gate charge(25nC max.)
- Low reverse transfer capacitance (C_{RSS} = 9pF typical)
- Fast switching capability
- 100% avalanche energy specified
- Improved dv/dt capability
- 150°C operation temperature

PRODUCT SUMMARY	
I_D (A)	4
V_{DSS} (V)	800
$R_{DS(ON)}$ (Ω)	3.6 @ V_{GS} = 10V
Q_G(nC) max.	25

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITIONS		VALUE	UNIT
V_{DSS}	Drain to Source voltage	T_J=25°C to 150°C		800	V
V_{DGR}	Drain to Gate voltage	R_{GS}=20KΩ		800	
V_{GS}	Gate to Source voltage			±30	
I_D	Continuous Drain Current	T_C=25°C		4	A
		T_C=100°C		2.5	
I_{DM}	Pulsed Drain current(Note 1)			15.6	
I_{AR}	Avalanche current(Note 1)			4	
E_{AR}	Repetitive avalanche energy(Note 1)	I_{AR}=4A, R_{GS}=50Ω, V_{GS}=10V		13	mJ
E_{AS}	Single pulse avalanche energy(Note 2)	I_{AS}=4A, L=57mH		460	
dv/dt	Peak diode recovery dv/dt(Note 3)			4.0	V /ns
P_D	Total power dissipation (Derate above 25°C)	T_C=25°C	TO-220AB	106 (0.85)	W(W/°C)
			TO-220F	36 (0.29)	
T_J	Operation junction temperature			-55 to 150	°C
T_{STG}	Storage temperature			-55 to 150	
T_L	Maximum soldering temperature, for 10 seconds	1.6mm from case		300	
	Mounting torque, #6-32 or M3 screw			10 (1.1)	lbf·in (N·m)

Note: 1.Repetitive rating: pulse width limited by junction temperature..

2.I_{AS} = 4A, V_{DD} = 50V, L = 57mH, R_{GS} = 25Ω, starting T_J=25°C.

3.I_{SD} ≤ 4A, di/dt ≤ 200A/μs, V_{DD} ≤ $V_{(BR)DSS}$, starting T_J=25°C.

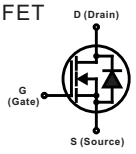
THERMAL RESISTANCE

SYMBOL	PARAMETER		Min.	Typ.	Max.	UNIT
$R_{th(j-c)}$	Thermal resistance, junction to case	TO-220AB			1.20	°C/W
		TO-220F			3.45	
$R_{th(j-a)}$	Thermal resistance, junction to ambient	TO-220AB/TO-220F			62.5	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITIONS		Min.	Typ.	Max.	UNIT
◎ OFF CHARACTERISTICS							
$V_{(BR)DSS}$	Drain to source breakdown voltage	I_D = 250μA ,V_{GS} = 0V		800			V
$\triangle V_{(BR)DSS}/\triangle T_J$	Breakdown voltage temperature coefficient	I_D = 250μA, V_{DS}=V_{GS}			0.95		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=800V, V_{GS}=0V	T_C = 25°C			10	μA
		V_{DS}=640V, V_{GS}=0V	T_C=125°C			100	
I_{GSS}	Gate to source forward leakage current	V_{GS} = 30V, V_{DS} = 0V				100	nA
	Gate to source reverse leakage current	V_{GS} = -30V, V_{DS} = 0V				-100	
◎ ON CHARACTERISTICS							
$R_{DS(ON)}$	Static drain to source on-state resistance	I_D =2A, V_{GS} = 10V			2.5	3.6	Ω
$V_{GS(TH)}$	Gate threshold voltage	V_{GS}=V_{DS}, I_D=250μA		3		5	V
g_{fs}	Forward transconductance (Note 1)	V_{DS}=50V, I_D=2A			3.8		S
◎ DYNAMIC CHARACTERISTICS							
C_{ISS}	Input capacitance	V_{DS} = 25V, V_{GS} = 0V, f =1MHz			680	880	pF
C_{OSS}	Output capacitance				75	100	
C_{RSS}	Reverse transfer capacitance				9	12	
◎ SWITCHING CHARACTERISTICS							
$t_{d(ON)}$	Turn-on delay time	V_{DD} = 400V, V_{GS} = 10V, I_D = 4A, R_{GS} = 25Ω (Note 1, 2)			16	40	ns
t_r	Rise time				45	100	
$t_{d(OFF)}$	Turn-off delay time				35	80	
t_f	Fall time				35	80	
Q_G	Total gate charge	V_{DD} = 640V, V_{GS} = 10V, I_D = 4A (Note 1, 2)			19	25	nC
Q_{GS}	Gate to source charge				4		
Q_{GD}	Gate to drain charge (Miller charge)				9		

SOURCE TO DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25°C unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITIONS	Min.	Typ.	Max.	UNIT
V_{SD}	Diode forward voltage	I_{SD} = 4A, V_{GS} = 0V			1.4	V
Is (I_{SD})	Continuous source to drain current	Integral reverse P-N junction diode in the MOSFET 			4	A
I_{SM}	Pulsed source current				15.6	
t_{rr}	Reverse recovery time	I_{SD} = 4A, V_{GS} = 0V, dI_F/dt = 100A/μs		580		ns
Q_{rr}	Reverse recovery charge			3.7		μC

Note: 1. Pulse test: Pulse width ≤ 300μs, duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

ORDERING INFORMATION SCHEME

4 N 80 A

Current rating, I_D

4 = 4A

MOSFET series

N = N-Channel

Voltage rating, V_{DS}

80 = 800V

Package type

A = TO-220AB

AF = TO-220F

Fig.1 On-region characteristics

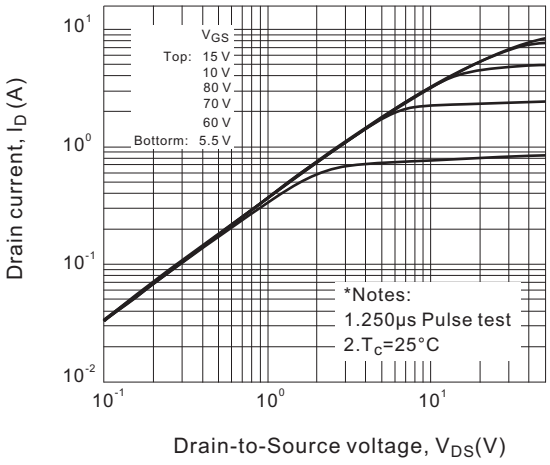


Fig.2 Transfer characteristics

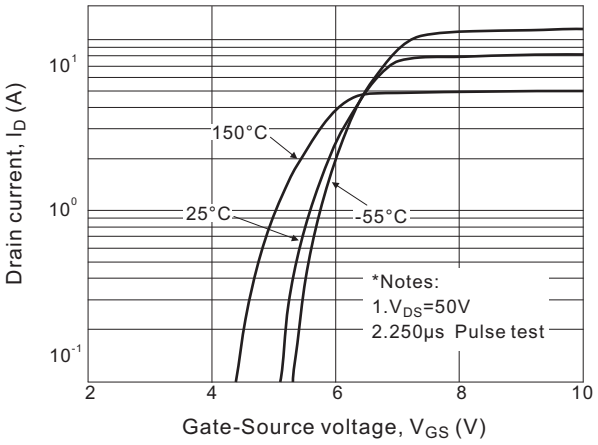


Fig.3 On-resistance variation vs. drain current and gate voltage

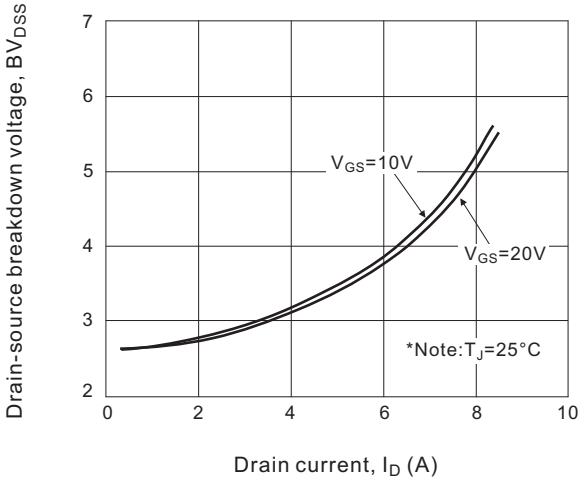


Fig.4 Body diode forward voltage variation vs. Source current and temperature

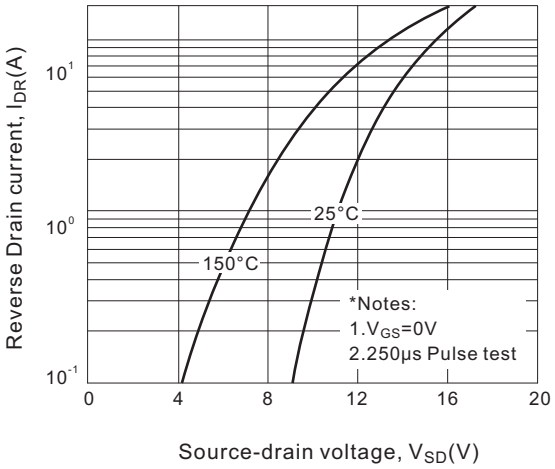


Fig.5 Capacitance characteristics

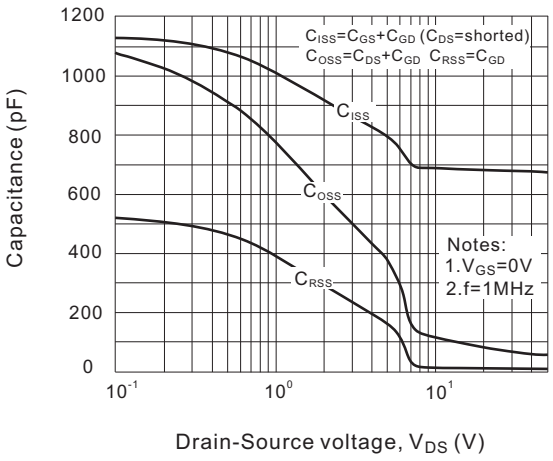


Fig.6 Gate charge characteristics

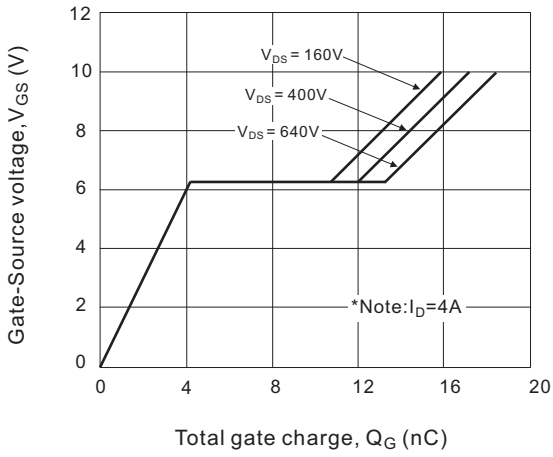


Fig.7 Breakdown voltage variation vs. temperature

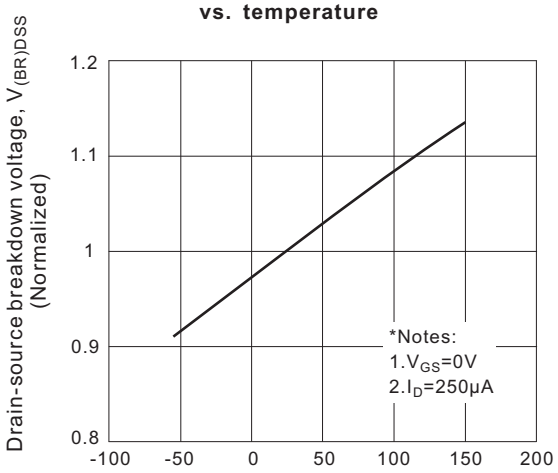


Fig.8 On-resistance vs. temperature

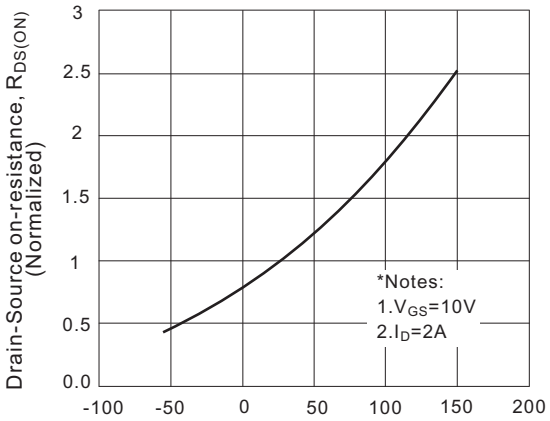


Fig.9-1 Maximum safe operating area for 4N80A

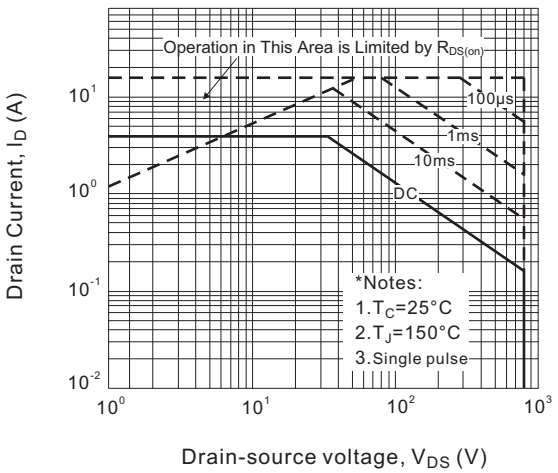


Fig.9-2 Transient thermal response curve for 4N80AF

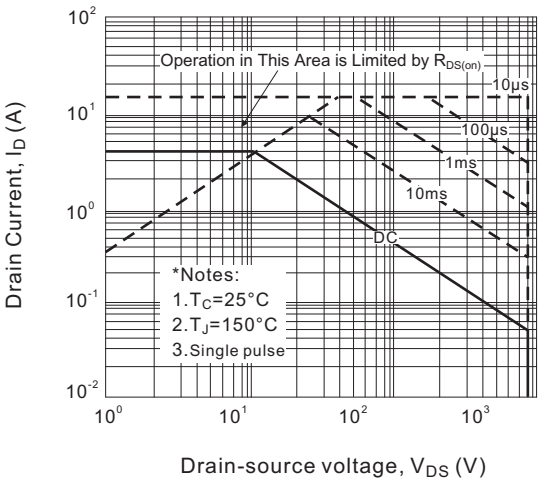


Fig.10 Maximum drain current vs. case temperature

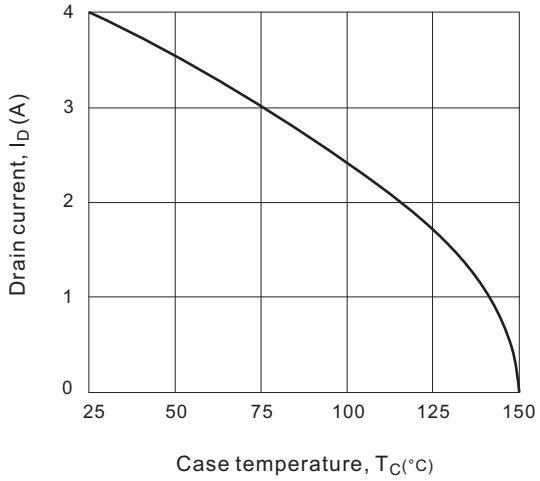


Fig.11-1 Transient Thermal Response Curve for 4N80A

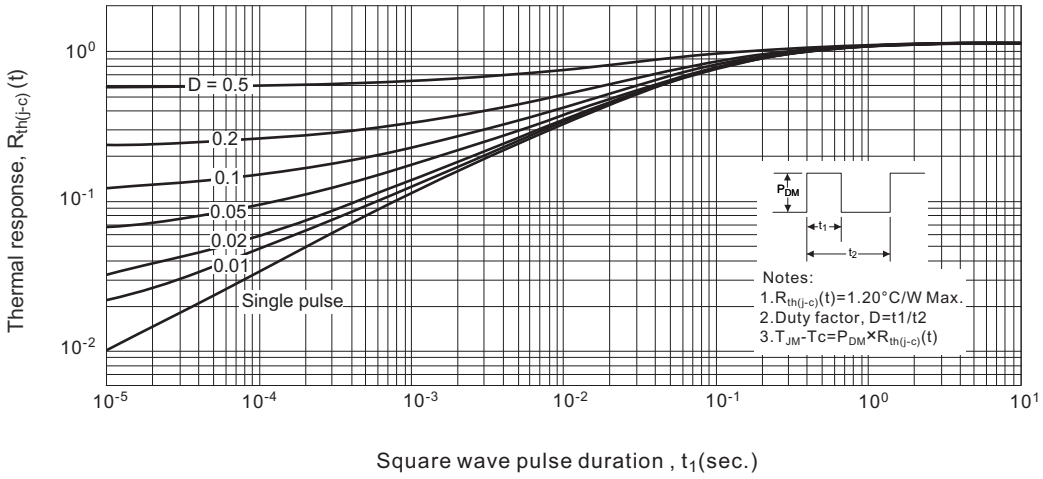
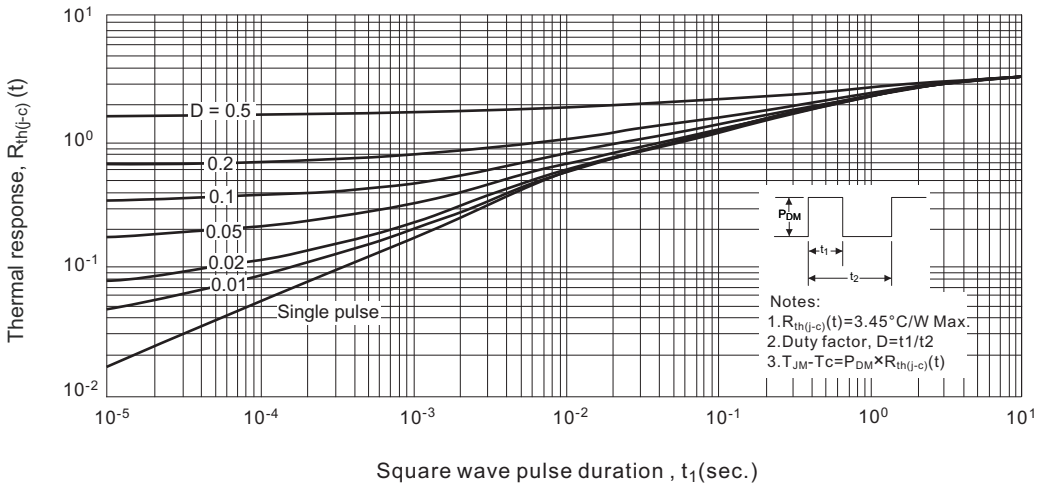


Fig.11-2 Transient Thermal Response Curve for 4N80AF



■ TEST CIRCUITS AND WAVEFORMS

Fig.1A Peak diode recovery dv/dt test circuit

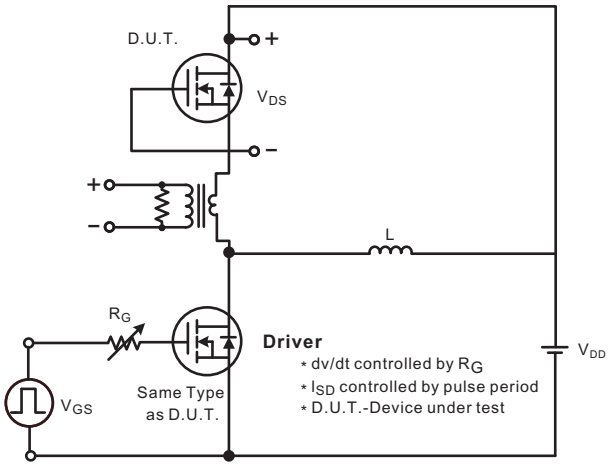


Fig.1B Peak diode recovery dv/dt waverforms

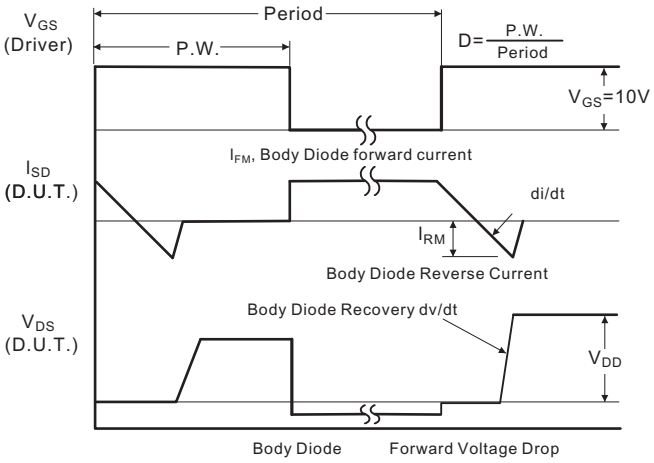


Fig.2A Switching test circuit

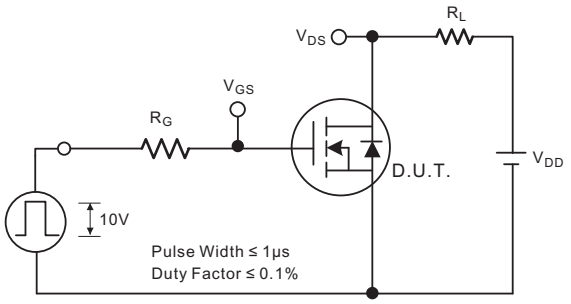


Fig.2B Switching Waveforms

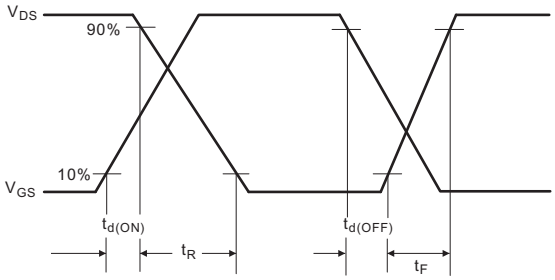


Fig.3A Gate charge test circuit

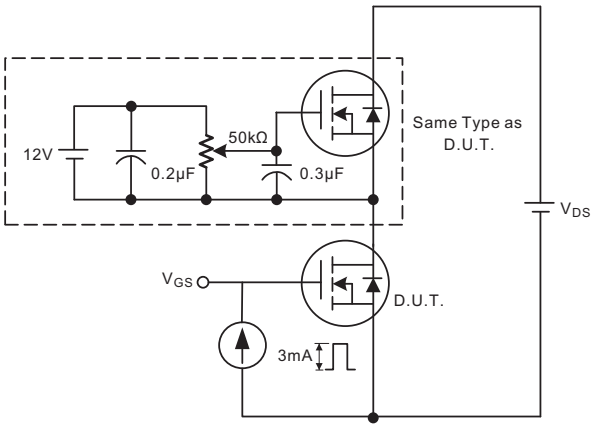


Fig.3B Gate charge waveform

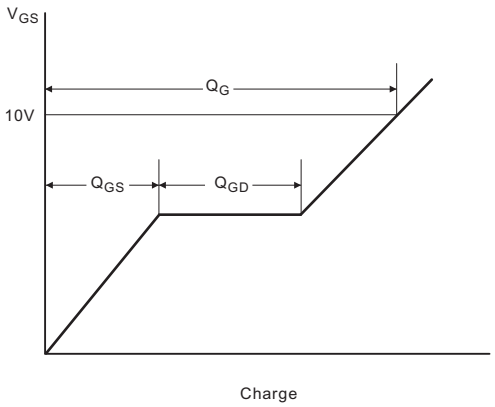


Fig.4A Unclamped Inductive switching test circuit

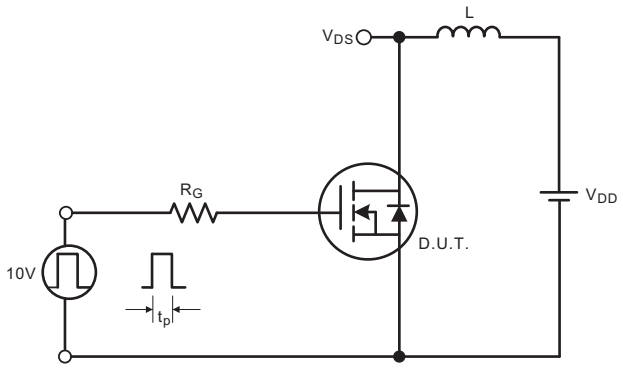
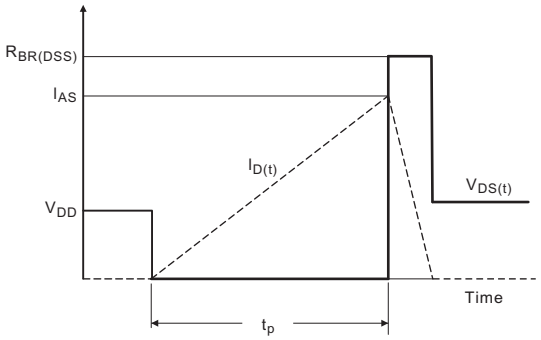


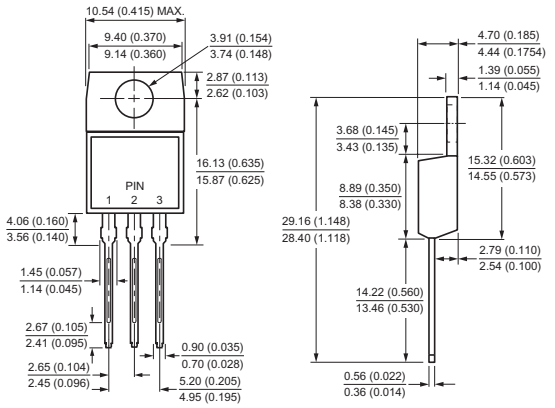
Fig.4B Unclamped Inductive switching waveforms

$$E_{AS} = \frac{1}{2} L \cdot I_{AS}^2 \cdot \frac{V_{BR(DSS)}}{V_{BR(DSS)} - V_{DD}}$$



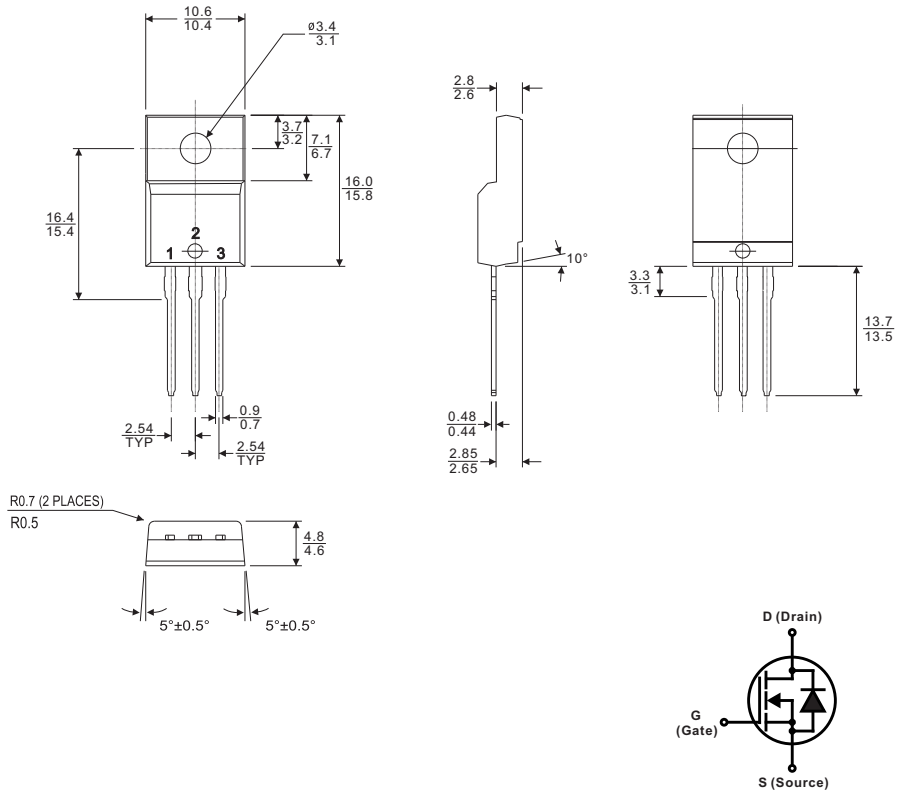
Case Style

TO-220AB



Case Style

TO-220F



All dimensions in millimeters